General Purpose Transistor

NPN Silicon

• Moisture Sensitivity Level: 1

• ESD Rating: Human Body Model: >4000 V

Machine Model: >400 V

• This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	65	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	265 2.1	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	470	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	640 5.1	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	195	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

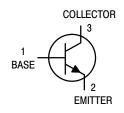
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



1B = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BC846BM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•	•	
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	65	_	_	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A$, $V_{EB} = 0$)	V _{(BR)CES}	80	_	_	٧
Collector – Base Breakdown Voltage (I _C = 10 μA)	V _{(BR)CBO}	80	_	-	٧
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	V _{(BR)EBO}	6.0	_	_	V
Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}	-	_ _	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h _{FE}	_ 200	150 290	_ 450	-
Collector – Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)	V _{CE(sat)}	-	- -	0.25 0.6	٧
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}		0.7 0.9	_ _	٧
Base – Emitter Voltage (I_C = 1.0 mA, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	550 580 -	645 660 –	700 700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	_	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Noise Figure ($I_C = 0.2 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz}, BW = 200 \text{ Hz})$	NF	_	_	10	dB

TYPICAL CHARACTERISTICS

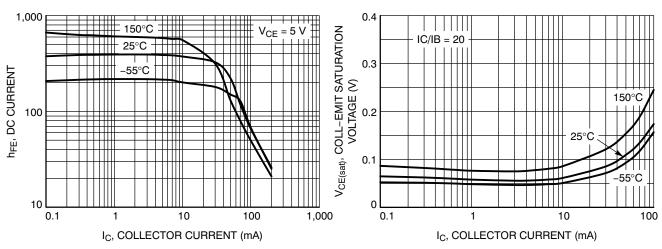


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

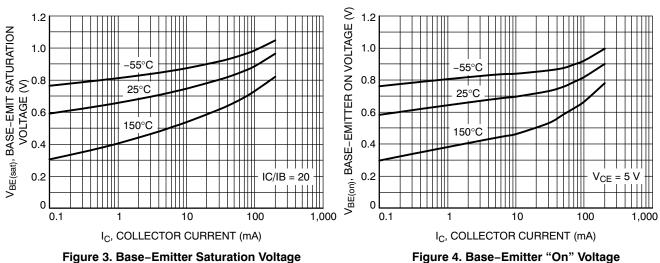


Figure 3. Base-Emitter Saturation Voltage

V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) TEMPERATURE COEFFICIENT (mV) 2.0 -0.2 -0.6 50 mA 100 mA 20 mA 1.6 10 mA -1.01.2 -1.4 -1.8 θ_{VB} , for V_{BE} 8.0 -2.2 0.4 -2.6-55°C to 150°C 0 0.1 10 100 1,000 0.01 I_C, COLLECTOR CURRENT (mA) IB, BASE CURRENT (mA)

Figure 5. Base-Emitter Temperature Coefficient

Figure 6. Collector Saturation Region

= 25°C

100

I_C = 200 mA

TYPICAL CHARACTERISTICS

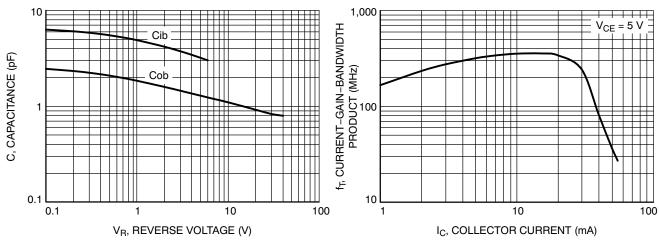
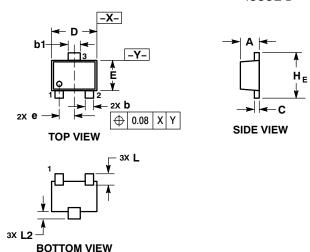


Figure 7. Capacitances

Figure 8. Current-Gain-Bandwidth Product

PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE D



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

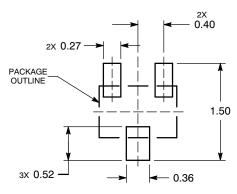
	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
E	0.75	0.80	0.85	
е	0.40 BSC			
ΗE	1.15	1.20	1.25	
L	0.29 REF			
12	0.15	0.20	0.25	

STYLE 1:

PIN 1. BASE 2. EMITTER

3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.